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(71) Applicant *(for all designated States except US)*: **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(72) Inventor; and

(75) Inventor/Applicant *(for US only)*: **MOFFATT, Stephen** [GB/GB]; The Barn, Ville Canut, Rue de la Corbiere, St. Brelade, Jersey, Channel Islands JE3 8QA (GB).

(74) Agents: **PATTERSON, B. Todd** et al.; Patterson & Sheridan, L.L.P., 3040 Post Oak Blvd., Suite 1500, Houston, Texas 77056-6582 (US).

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(54) **Title**: CRYSTALLIZATION PROCESSING FOR SEMICONDUCTOR APPLICATIONS

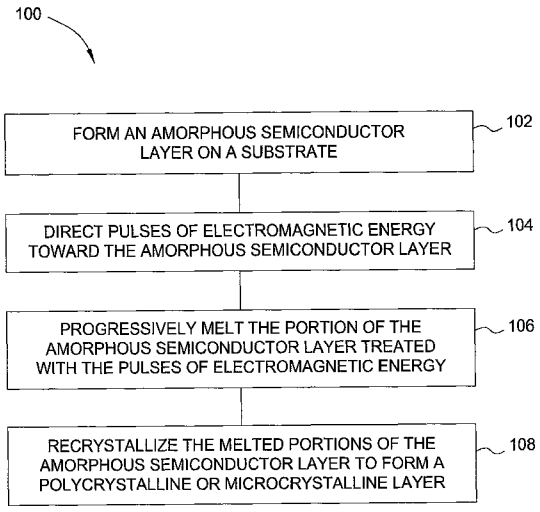


FIG. 1A

(57) **Abstract**: A method and apparatus for forming a crystalline semiconductor layer on a substrate are provided. A semiconductor layer is formed by vapor deposition. A pulsed laser melt/recrystallization process is performed to convert the semiconductor layer to a crystalline layer. Laser, or other electromagnetic radiation, pulses are formed into a pulse train and uniformly distributed over a treatment zone, and successive neighboring treatment zones are exposed to the pulse train to progressively convert the deposited material to crystalline material.

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